

2SA900

Silicon PNP Epitaxial Planar Type

AF Power Amplifier
Complementary Pair with 2SC1568

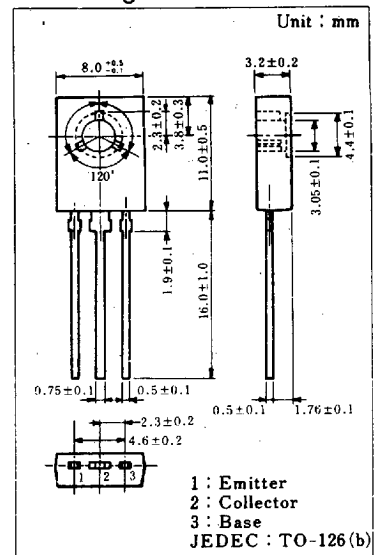
Features

- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- TO-126 package, no insulator needed when fixing to a heat sink

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-18	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-2	A
Collector current	I_C	-1	A
Collector power dissipation	P_C	1.2	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

Package Dimensions



Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -10\text{ V}, I_E = 0$			-1	μA
	I_{CEO}	$V_{CE} = -18\text{ V}, I_B = 0$			-10	
Collector-base voltage	V_{CBO}	$I_C = -10\ \mu\text{A}, I_E = 0$	-20			V
Collector-emitter voltage	V_{CEO}	$I_C = -1\text{ mA}, I_B = 0$	-18			V
Emitter-base voltage	V_{EBO}	$I_E = -10\ \mu\text{A}, I_C = 0$	-5			V
DC current gain	h_{FE1}^*	$V_{CE} = -2\text{ V}, I_C = -500\text{ mA}$	90		360	
	h_{FE2}	$V_{CE} = -2\text{ V}, I_C = -1.5\text{ A}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{ A}, I_B = -50\text{ mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$			-1.2	V
Transition frequency	f_T	$V_{CB} = -6\text{ V}, I_E = 50\text{ mA}, f = 200\text{ MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{ V}, I_E = 0, f = 1\text{ MHz}$		40		pF

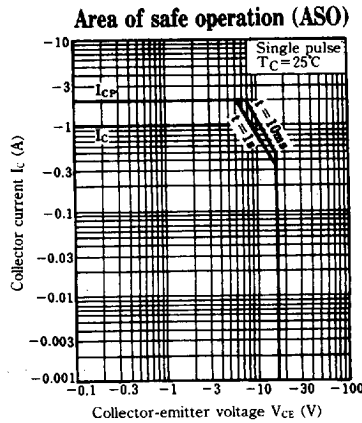
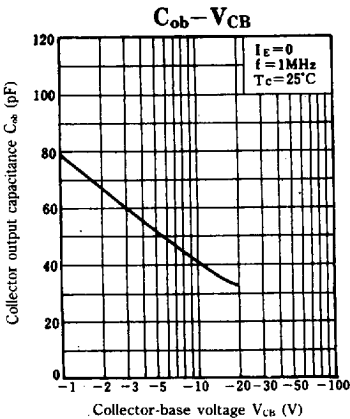
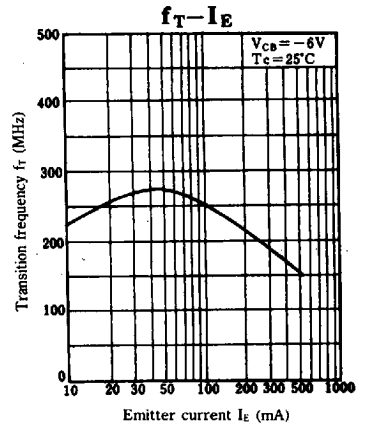
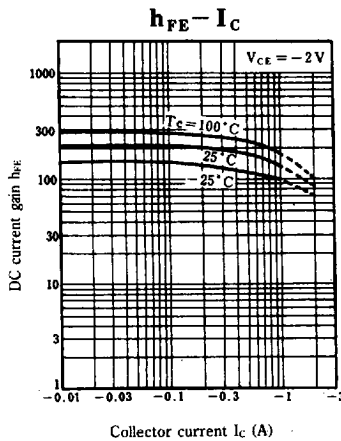
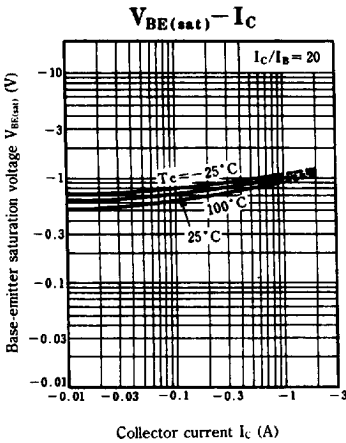
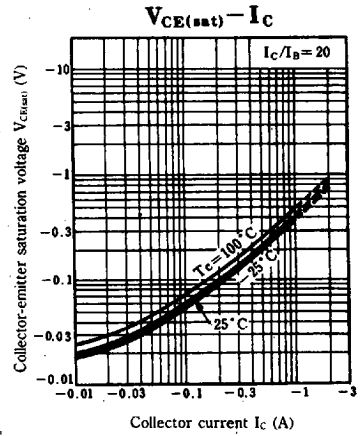
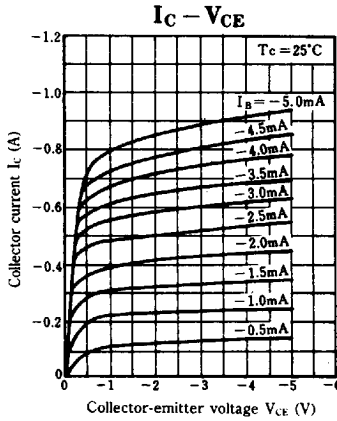
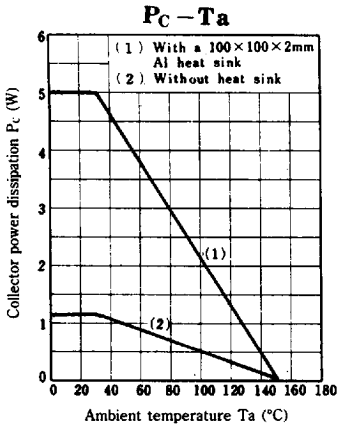
* h_{FE1} Classifications

Class	Q	R	S	T
h_{FE1}	90 ~ 155	130 ~ 210	180 ~ 280	250 ~ 360

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Panasonic

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